

2SC2611

Silicon NPN Triple Diffused

HITACHI

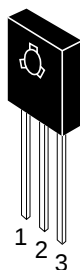
ADE-208-884 (Z)
1st. Edition
Sep. 2000

Application

High voltage amplifier TV VIDEO output

Outline

TO-126 MOD



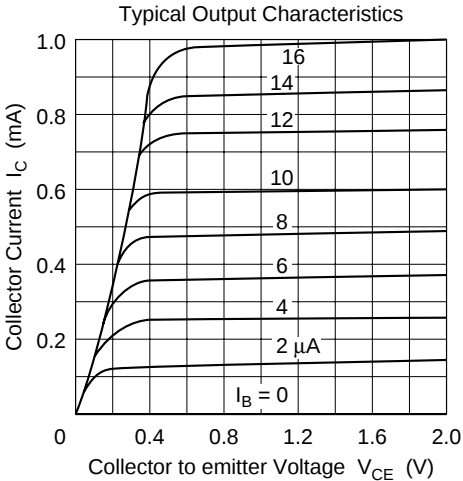
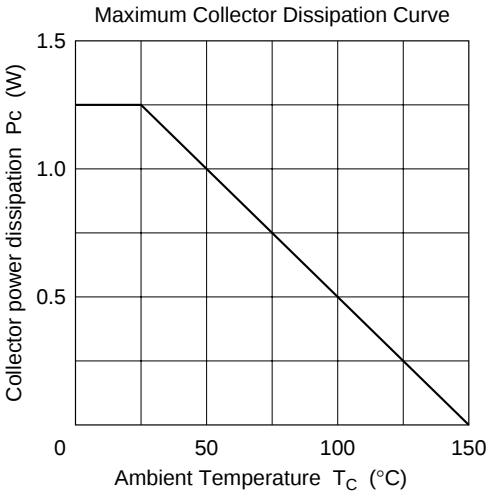
1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

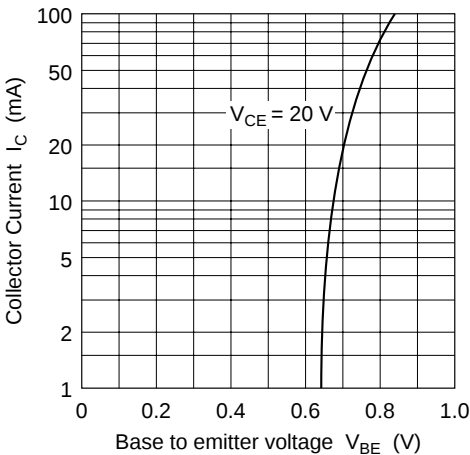
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V_{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_{C}	100	mA
Collector power dissipation	P_{C}	1.25	W
Junction temperature	T_{j}	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics (Ta = 25°C)

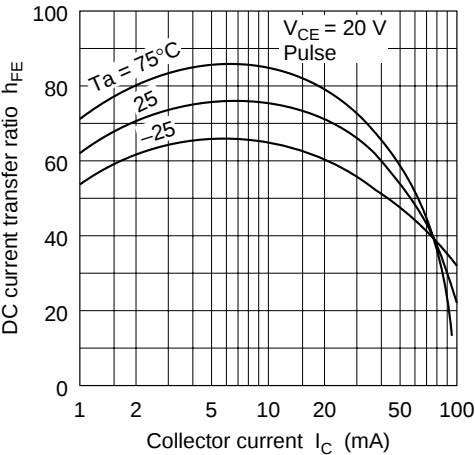
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CEO}	—	—	1.0	μA	$V_{CE} = 250\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	30	—	200		$V_{CE} = 20\text{ V}$, $I_C = 20\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 20\text{ mA}$, $I_B = 2\text{ mA}$
Gain bandwidth product	f_T	50	80	—	MHz	$V_{CE} = 20\text{ V}$, $I_C = 20\text{ mA}$
Collector output capacitance	C_{ob}	—	—	4.0	pF	$V_{CB} = 20\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$



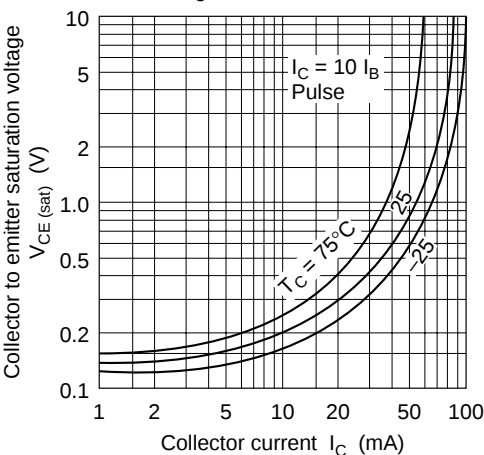
Typical Transfer Characteristics



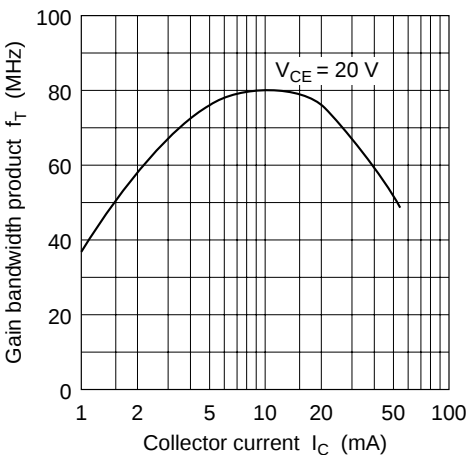
DC Current Transfer Ratio vs. Collector Current

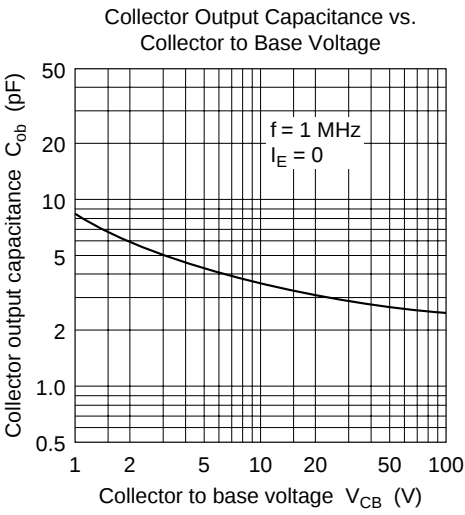


Collector to Emitter Saturation Voltage vs. Collector Current



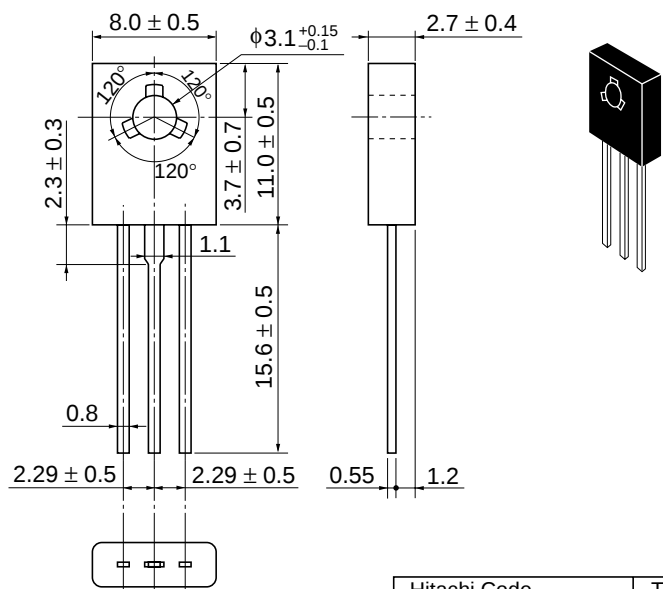
Gain Bandwidth Product vs. Collector Current





Package Dimensions

Unit: mm



Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Mass (reference value)	0.67 g

Cautions

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